

MOSFETs Silicon N-Channel MOS (U-MOSVI-H)

TPCP8205-H

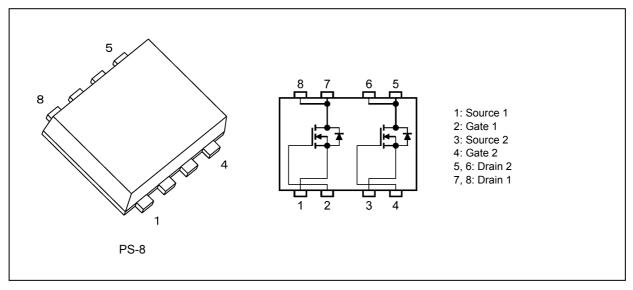
1. Applications

- · Motor Drivers
- · Mobile Equipment

2. Features

- (1) Small footprint due to a small and thin package
- (2) High-speed switching
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 20 \text{ m}\Omega$ (typ.)($V_{GS} = 10 \text{ V}$)
- (4) Low leakage current: I_{DSS} = 10 μA (max) (V_{DS} = 30 V)
- (5) Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_{D} = 0.1 mA)

3. Packaging and Internal Circuit





4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics | Symbol | Rating | Unit | | |
|---|-----------|--------------------|-------------------|------------|----|
| Drain-source voltage | | | V_{DSS} | 30 | V |
| Gate-source voltage | | | V_{GSS} | ±20 | |
| Drain current (DC) | | (Note 1) | I_D | 6.5 | Α |
| Drain current (pulsed) | | (Note 1) | I _{DP} | 26 | |
| Power dissipation (single operation) | (t = 5 s) | (Note 2), (Note 4) | P _{D(1)} | 1.48 | W |
| Power dissipation (per device for dual operation) | (t = 5 s) | (Note 2), (Note 5) | P _{D(2)} | 1.23 | |
| Power dissipation (single operation) | (t = 5 s) | (Note 3), (Note 4) | P _{D(1)} | 0.58 | |
| Power dissipation (per device for dual operation) | (t = 5 s) | (Note 3), (Note 5) | P _{D(2)} | 0.36 | |
| Single-pulse avalanche energy | | (Note 6) | E _{AS} | 10.9 | mJ |
| Avalanche current | | | I _{AR} | 6.5 | Α |
| Repetitive avalanche energy | | (Note 2), (Note 7) | E _{AR} | 0.032 | mJ |
| Channel temperature | | | T _{ch} | 150 | °C |
| Storage temperature | | | T _{stg} | -55 to 150 |] |

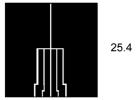
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

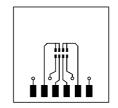
5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit | | |
|---|-----------|--------------------|--------------------------|-------|------|
| Channel-to-ambient thermal resistance (single operation) | (t = 5 s) | (Note 2), (Note 4) | R _{th(ch-a)(1)} | 84.5 | °C/W |
| Channel-to-ambient thermal resistance (per device for dual operation) | (t = 5 s) | (Note 2), (Note 5) | R _{th(ch-a)(2)} | 101.6 | |
| Channel-to-ambient thermal resistance (single operation) | (t = 5 s) | (Note 3), (Note 4) | R _{th(ch-a)(1)} | 215.5 | |
| Channel-to-ambient thermal resistance (per device for dual operation) | (t = 5 s) | (Note 3), (Note 5) | R _{th(ch-a)(2)} | 347.2 |] |

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1
- Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2
- Note 4: Power dissipation and thermal resistance values per device with the other device being off (During single operation, power is supplied to only one of the two devices.)
- Note 5: Power dissipation and thermal resistance values per device for dual operation (During dual operation, power is evenly supplied to both devices.)
- Note 6: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.2 mH, R_{G} = 25 Ω , I_{AR} = 6.5 A
- Note 7: Repetitive rating; pulse width limited by maximum channel temperature.



 $\begin{aligned} & \text{FR-4} \\ 25.4 \times 25.4 \times 0.8 \\ & \text{(Unit: mm)} \end{aligned}$



 $\begin{aligned} & \text{FR-4} \\ 25.4 \times 25.4 \times 0.8 \\ & \text{(Unit: mm)} \end{aligned}$

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



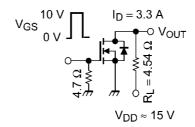
6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±0.1 | μΑ |
| Drain cut-off current | I _{DSS} | V _{DS} = 30 V, V _{GS} = 0 V | | | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | $I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$ | 30 | | | V |
| Drain-source breakdown voltage | V _{(BR)DSX} | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$ | 15 | | | |
| Gate threshold voltage | V_{th} | $V_{DS} = 10 \text{ V}, I_{D} = 0.1 \text{ mA}$ | 1.3 | | 2.3 | |
| Drain-source on-resistance | R _{DS(ON)} | $V_{GS} = 4.5 \text{ V}, I_D = 3.3 \text{ A}$ | | 22 | 29 | mΩ |
| | | V_{GS} = 10 V, I_D = 3.3 A | _ | 20 | 26 | |
| Forward transfer admittance | Y _{fs} | V _{DS} = 10 V, I _D = 3.3 A | 7.5 | 15 | _ | S |

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz | _ | 830 | _ | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 53 | | |
| Output capacitance | C _{oss} | | _ | 177 | | |
| Switching time (rise time) | t _r | See Figure 6.2.1. | _ | 4.1 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 10.8 | _ | |
| Switching time (fall time) | t _f | | _ | 11 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 31 | | |



Duty \leq 1%, $t_W = 10 \ \mu s$

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6.5 \text{ A}$ | | 13.8 | _ | nC |
| Gate-source charge 1 | Q _{gs1} | | _ | 3 | _ | |
| Gate-drain charge | Q_{gd} | | | 2.3 | _ | |

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------|------------------|--|-----|------|------|------|
| Reverse drain current (pulsed) | (Note 8) | I _{DRP} | _ | | | 26 | Α |
| Diode forward voltage | | V_{DSF} | I _{DR} = 6.5 A, V _{GS} = 0 V | | | -1.2 | V |

Note 8: Ensure that the channel temperature does not exceed 150°C.



7. Marking

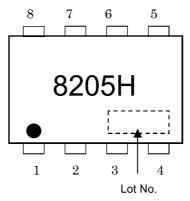
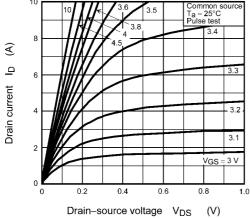


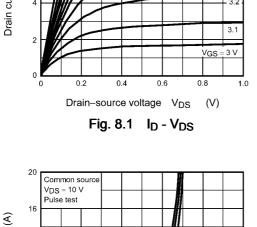
Fig. 7.1 Marking

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8. Characteristics Curves (Note)





Drain current 8 0 L

Fig. 8.3 I_D - V_{GS}

Gate-source voltage VGS

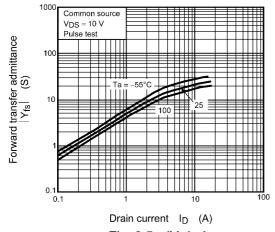


Fig. 8.5 |Y_{fs}| - I_D

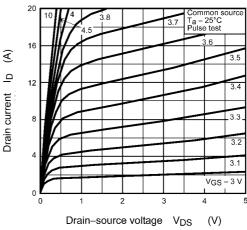


Fig. 8.2 I_D - V_{DS}

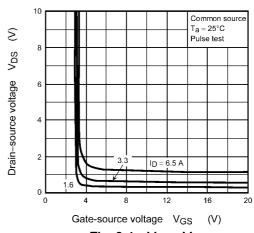


Fig. 8.4 V_{DS} - V_{GS}

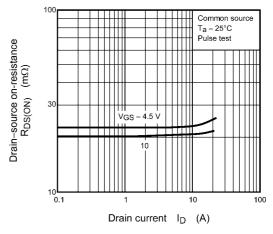


Fig. 8.6 R_{DS(ON)} - I_D

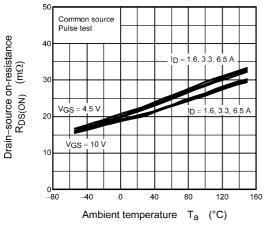


Fig. 8.7 R_{DS(ON)} - T_a

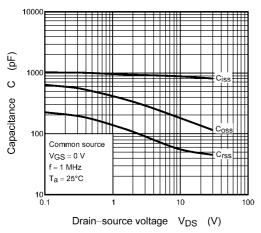


Fig. 8.9 Capacitance - V_{DS}

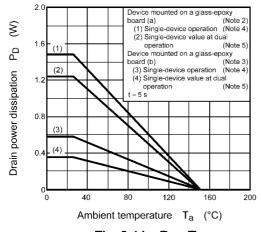


Fig. 8.11 P_D - T_a (Guaranteed Maximum)

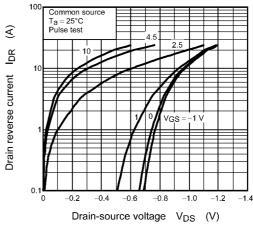


Fig. 8.8 IDR - VDS

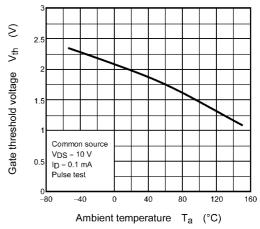


Fig. 8.10 V_{th} - T_a

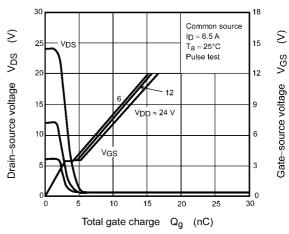


Fig. 8.12 Dynamic Input/Output Characteristics

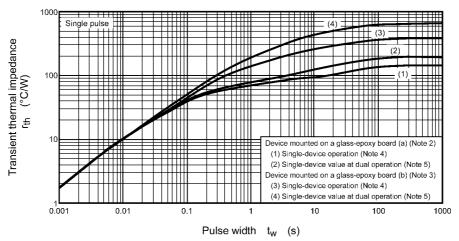


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

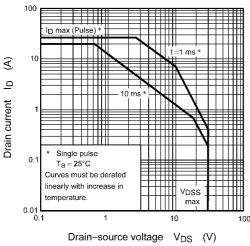


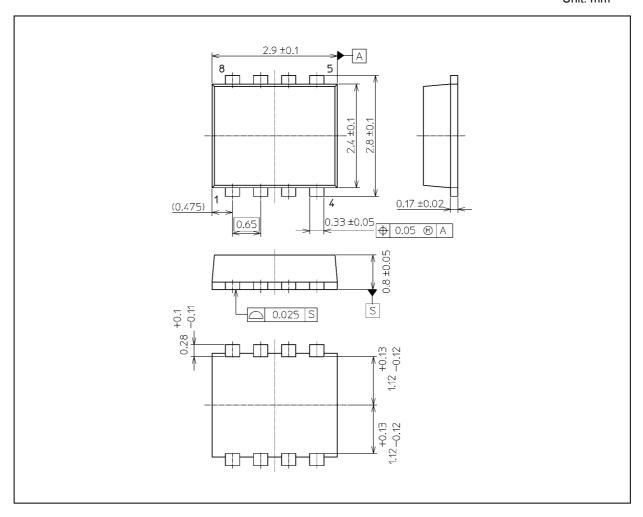
Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.017 g (typ.)

| | Package Name(s) |
|-----------------|-----------------|
| TOSHIBA: 2-3V1S | |
| Nickname: PS-8 | |



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